

GSDBAW56

Monolithic Dual Switching Diode Common Anode

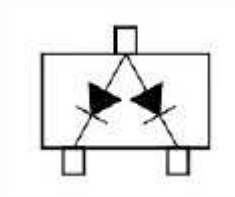
Product Description

Switching Diode 215mA / 75V

Features

- Low forward voltage
- Fast reverse recovery time
- Lead(Pb)-Free

Packages

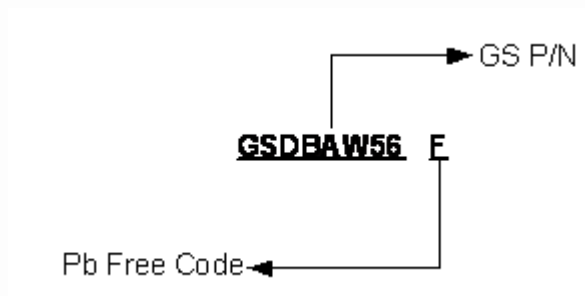


SOT- 23

Marking Information

Part Number	Package	Part Marking
GSDBAW56F	SOT- 23	A1

Ordering Information



Part Number	Package	Quantity
GSDBAW56F	SOT- 23	3000 PCS

GSDBAW56

Maximum Ratings

($T_A=25^{\circ}\text{C}$ Unless otherwise noted)

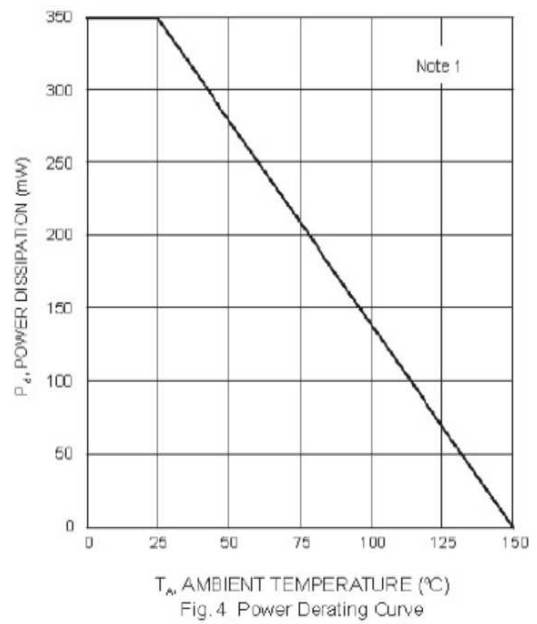
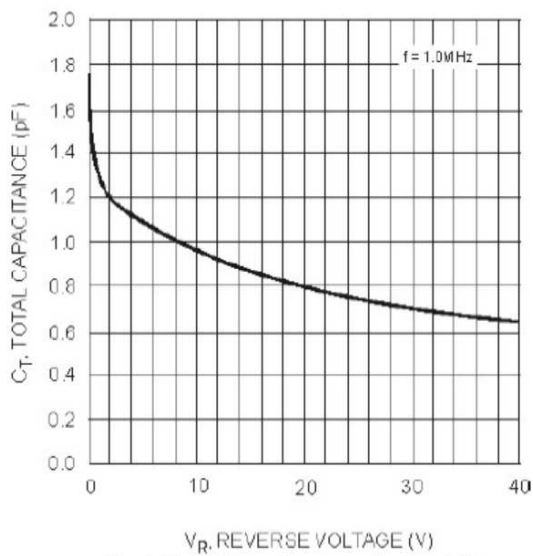
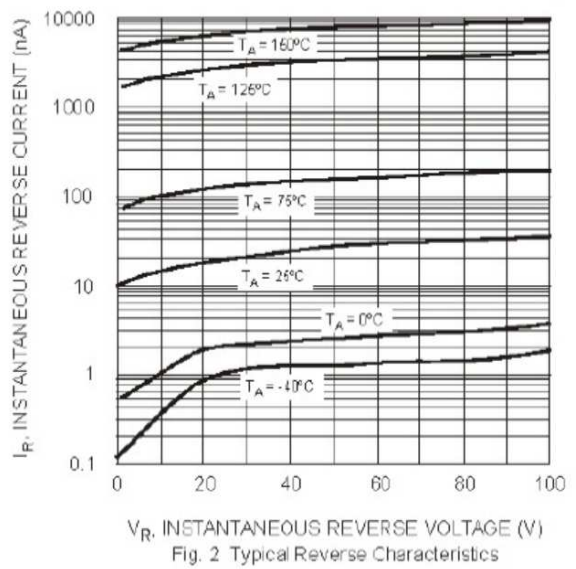
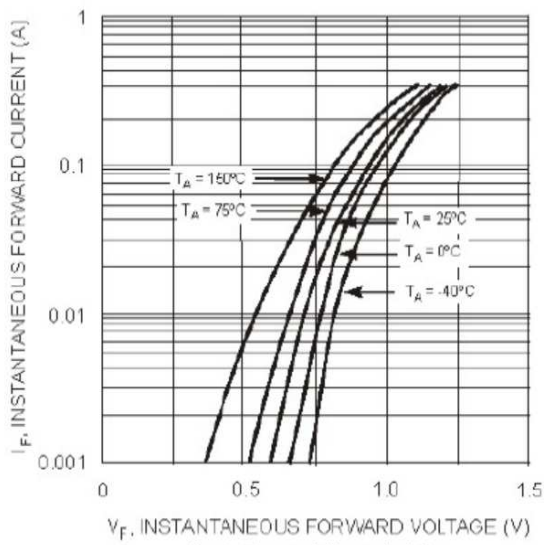
Symbol	Conditions	Value	Unit
V_{RRM}	Peak Repetitive Reverse Voltage	85	V
V_R	Reverse Voltage	75	V
I_F	Forward Current	215	mA
I_{FSM}	Peak Forward Surge Current, $t = 1\text{s}$ $t = 1\mu\text{s}$	0.5 4	A
P_D	Total Power Dissipation(Note1)	350	mW
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-55 to +150	$^{\circ}\text{C}$

Electrical Characteristics

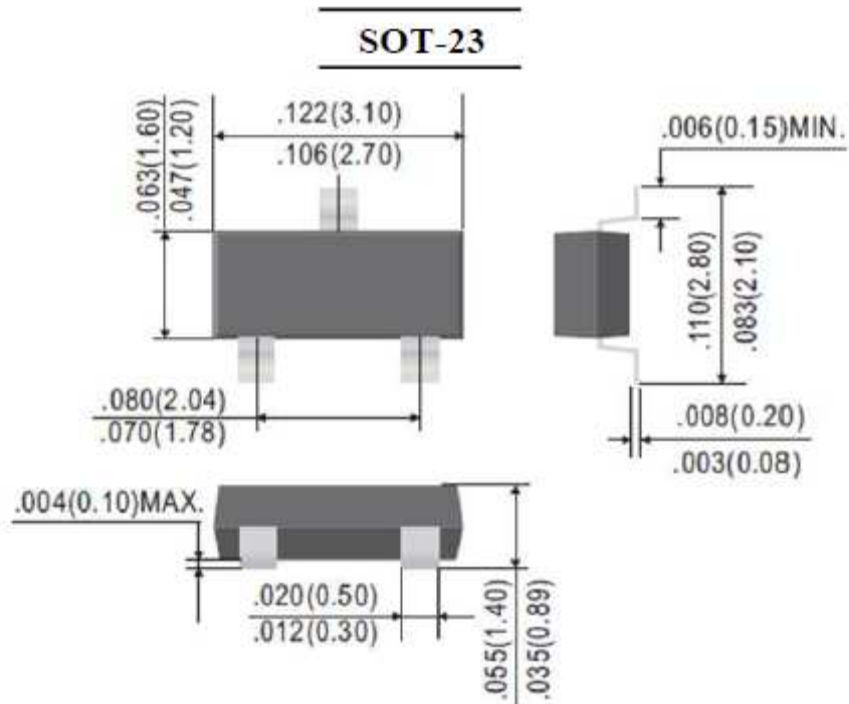
($T_A=25^{\circ}\text{C}$ Unless otherwise noted)

Symbol	Conditions	Max	Unit
V_F	Forward Voltage ($I_F=1.0\text{mA}$)	715	mV
	($I_F=10\text{mA}$)	855	
	($I_F=50\text{mA}$)	1000	
	($I_F=150\text{mA}$)	1250	
I_R	Reverse Current , $V_R=25\text{V}$	30	nA
	Reverse Current , $V_R=75\text{V}$	1	μA
	Reverse Current , ($V_R=25\text{V}$, $T_J=150^{\circ}\text{C}$)	30	
	Reverse Current , ($V_R=70\text{V}$, $T_J=150^{\circ}\text{C}$)	50	
C_d	Diode Capacitance ($V_R=0\text{V}$, $f=1.0\text{MHz}$),	2	pF
T_{rr}	Reverse Recovery Time $I_F=10\text{mA}$, $V_R=6\text{V}$, $I_{rr}=1\text{mA}$, $R_L=100\Omega$	4	ns

Typical Characteristics



Package Dimension









Dimensions in inches and (millimeter)

NOTICE

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CONTACT US

GS Headquarter	
	4F.,No.43-1,Lane11,Sec.6,Minquan E.Rd Neihu District Taipei City 114, Taiwan (R.O.C)
	886-2-2657-9980
	886-2-2657-3630
	sales_twn@gs-power.com

RD Division	
	824 Bolton Drive Milpitas. CA. 95035
	1-408-457-0587